

# STB20NM60-1 - STP20NM60FP STB20NM60 - STP20NM60 - STW20NM60

N-channel 600V - 0.25Ω - 20A - TO-247 - TO-220/FP - D<sup>2</sup>/I<sup>2</sup>PAK MDmesh™ Power MOSFET

#### **Features**

Туре	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STP20NM60	600V	< 0.29Ω	20A
STP20NM60FP	600V	$< 0.29\Omega$	20A
STB20NM60	600V	< 0.29Ω	20A
STB20NM60-1	600V	$< 0.29\Omega$	20A
STW20NM60	600V	< 0.29Ω	20A

- High dv/dt and avalanche capabilities
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance



■ Switching applications

## **Description**

The MDmesh™ is a new revolutionary Power MOSFET technology that associates the multiple drain process with the company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

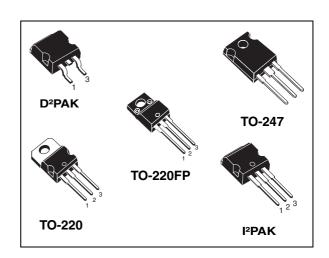


Figure 1. Internal schematic diagram

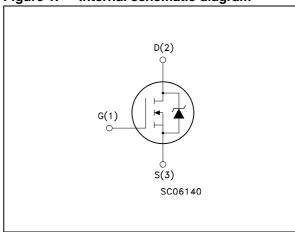


Table 1. Device summary

Part number	Marking	Package	Packaging
STP20NM60	P20NM60	TO-220	Tube
STP20NM60FP	P20NM60FP	TO-220FP	Tube
STB20NM60T4	B20NM60	D²PAK	Tape & reel
STB20NM60-1	B20NM60-1	I <sup>2</sup> PAK	Tube
STW20NM60	W20NM60	TO-247	Tube

# **Contents**

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	6
3	Test circuit	9
4	Package mechanical data	0
5	Packaging mechanical data1	6
6	Revision history 1	7

# 1 Electrical ratings

Table 2. Absolute maximum ratings

		Valu	е			
Symbol	Parameter	TO-220/D <sup>2</sup> PAK I <sup>2</sup> PAK/TO-247	TO-220FP	Unit		
V <sub>DS</sub>	Drain-source voltage (V <sub>GS</sub> = 0)	600		V		
V <sub>GS</sub>	Gate- source voltage	±30	)	V		
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25°C	20	20 <sup>(1)</sup>	Α		
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100°C	12.6 12.6 <sup>(1)</sup>		Α		
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	80	80 <sup>(1)</sup>	Α		
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25°C	192	45	W		
	Derating factor	1.5	0.36	W/°C		
dv/dt (3)	Peak diode recovery voltage slope	15		V/ns		
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s;T <sub>C</sub> =25°C)	2500				V
T <sub>stg</sub>	Storage temperature	-65 to 150		°C		
T <sub>j</sub>	Max. operating junction temperature	150	)	°C		

- 1. Limited only by maximum temperature allowed
- 2. Pulse width limited by safe operating area
- 3.  $I_{SD} \le 20A$ , di/dt  $\le 400A/\mu s$ ,  $V_{DD} \le V_{(BR)/DSS}$ ,  $Tj \le T_{JMAX}$

Table 3. Thermal resistance

Symbol	Parameter	TO-220/D²PAK I²PAK/TO-247 TO-220FP		Unit
Rthj-case	Thermal resistance junction-case max	0.65 2.8		°C/W
Rthj-amb	Thermal resistance junction-ambient max	62.5		°C/W
T <sub>I</sub>	Maximum lead temperature for soldering purpose	300		°C

Table 4. Avalanche data

Symbol	Parameter	Max. value	Unit
I <sub>AS</sub>	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ max)	10	Α
E <sub>AS</sub>	Single pulse avalanche energy (starting $T_j = 25$ °C, $I_D = I_{AS}$ , $V_{DD} = 50$ V)	650	mJ

# 2 Electrical characteristics

(T<sub>CASE</sub>=25°C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	$I_D = 250 \ \mu A, \ V_{GS} = 0$	600			V
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	$V_{DS}$ = Max rating $V_{DS}$ = Max rating, @ 125°C			1 10	μ <b>Α</b> μ <b>Α</b>
I <sub>GSS</sub>	Gate-body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 30V			±100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3	4	5	V
R <sub>DS(on)</sub>	Static drain-source on resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 10 A		0.25	0.29	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
9 <sub>fs</sub> <sup>(1)</sup>	Forward transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max},$ $I_D = 10 \text{ A}$		11		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$		1500 350 35		pF pF pF
C <sub>oss eq.</sub> (2)	Equivalent output capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 480 V		215		pF
$egin{array}{c} Q_{g} \ Q_{gs} \ Q_{gd} \end{array}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 10 \text{ V}$ (see Figure 16)		39 10 20	54	nC nC nC
R <sub>g</sub>	Gate input resistance	f = 1 MHz Gate DC bias=0 Test signal level = 20 mV open drain		1.6		Ω

<sup>1.</sup> Pulsed: Pulse duration = 300  $\mu$ s, duty cycle 1.5 %

<sup>2.</sup>  $C_{oss\ eq.}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD}$ = 300 V, $I_{D}$ = 10 A $R_{G}$ = 4.7 $\Omega$ $V_{GS}$ = 10 V (see Figure 15)		25 20 42 11		ns ns ns ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Тур.	Max	Unit
I <sub>SD</sub>	Source-drain current Source-drain current (pulsed)				20 80	A A
V <sub>SD</sub> <sup>(2)</sup>	Forward on voltage	I <sub>SD</sub> = 20 A, V <sub>GS</sub> = 0			1.5	V
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	I <sub>SD</sub> =20A, di/dt=100A/μs, V <sub>DD</sub> = 60 V (see Figure 20)		390 5 25		ns µC A
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}$ =20A, di/dt=100A/ $\mu$ s, $T_j$ = 150°C, $V_{DD}$ = 60 V (see Figure 20)		510 6.5 26		ns µC A

<sup>1.</sup> Pulse width limited by safe operating area

<sup>2.</sup> Pulsed: Pulse duration = 300  $\mu$ s, duty cycle 1.5 %

### 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220 / D<sup>2</sup>PAK / I<sup>2</sup>PAK

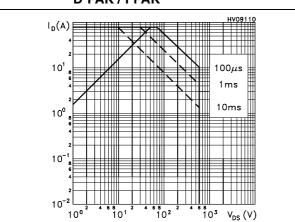


Figure 3. Thermal impedance for TO-220 / D<sup>2</sup>PAK / I<sup>2</sup>PAK

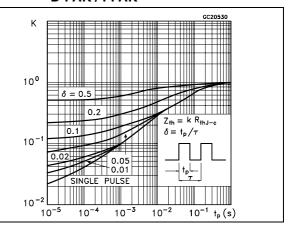
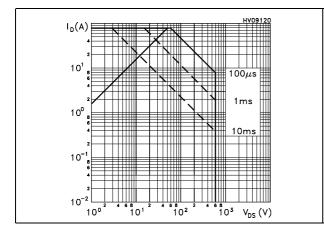


Figure 4. Safe operating area for TO-220FP

Figure 5. Thermal impedance for TO-220FP



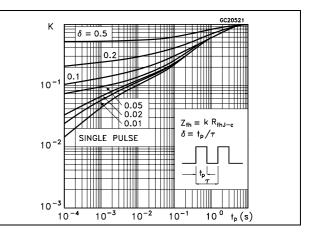
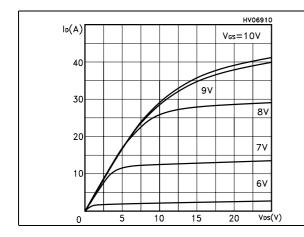


Figure 6. Output characterisics

Figure 7. Transfer characteristics



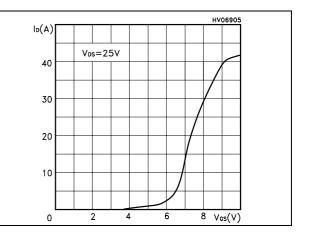


Figure 8. Transconductance

Figure 9. Static drain-source on resistance

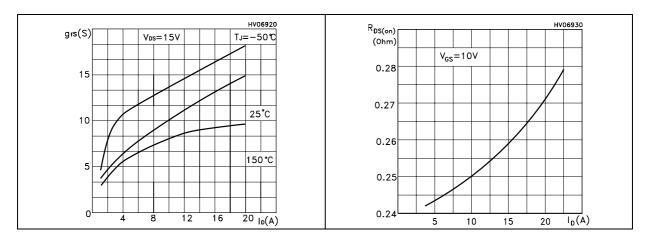


Figure 10. Gate charge vs gate-source voltage Figure 11. Capacitance variations

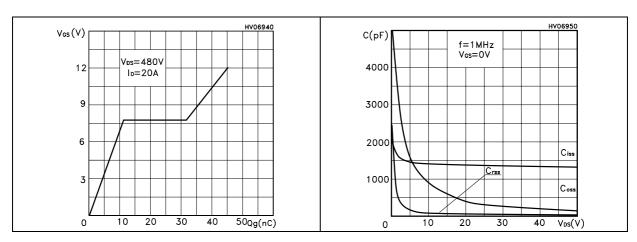


Figure 12. Normalized gate threshold voltage Figure 13. Normalized on resistance vs vs temperature temperature

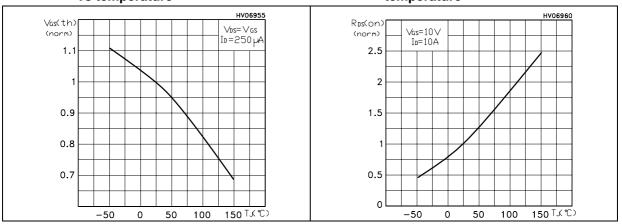
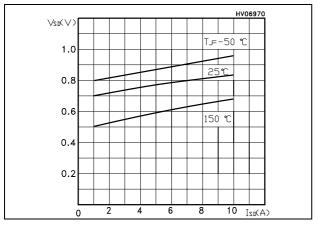


Figure 14. Source-drain diode forward characteristics



# 3 Test circuit

Figure 15. Switching times test circuit for resistive load

Figure 16. Gate charge test circuit

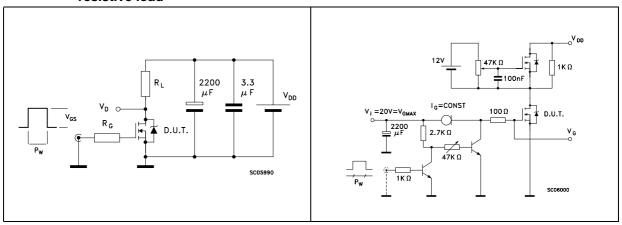


Figure 17. Test circuit for inductive load switching and diode recovery times

Figure 18. Unclamped inductive load test circuit

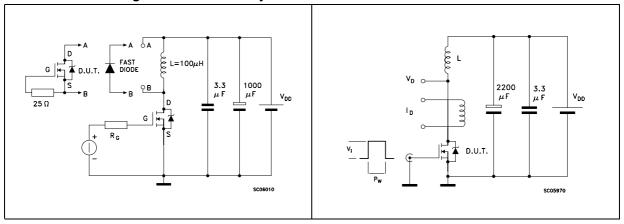
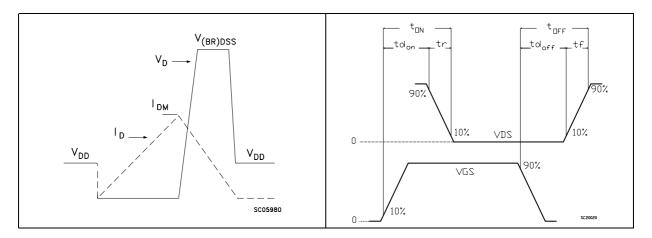


Figure 19. Unclamped inductive waveform

Figure 20. Switching time waveform

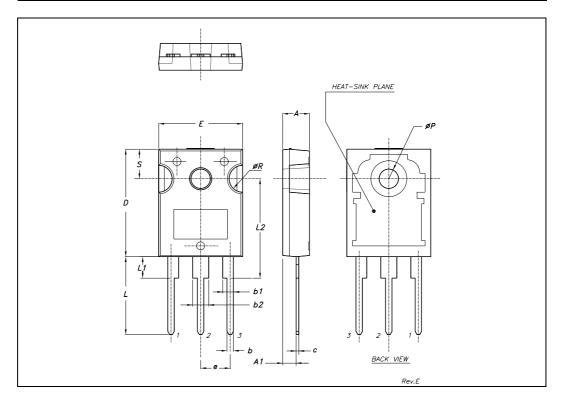


# 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: <a href="https://www.st.com">www.st.com</a>

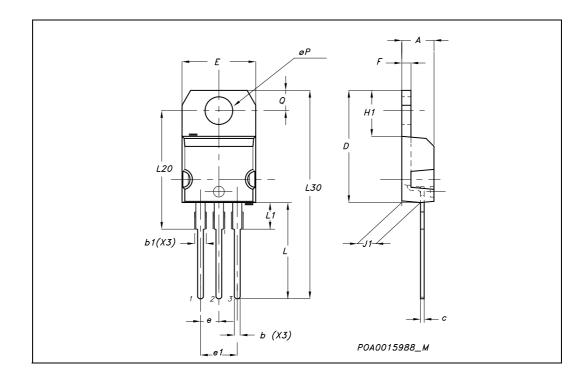
#### **TO-247 MECHANICAL DATA**

DIM.		mm.		inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
Α	4.85		5.15	0.19		0.20	
A1	2.20		2.60	0.086		0.102	
b	1.0		1.40	0.039		0.055	
b1	2.0		2.40	0.079		0.094	
b2	3.0		3.40	0.118		0.134	
С	0.40		0.80	0.015		0.03	
D	19.85		20.15	0.781		0.793	
E	15.45		15.75	0.608		0.620	
е		5.45			0.214		
L	14.20		14.80	0.560		0.582	
L1	3.70		4.30	0.14		0.17	
L2		18.50			0.728		
øΡ	3.55		3.65	0.140		0.143	
øR	4.50		5.50	0.177		0.216	
S		5.50			0.216		



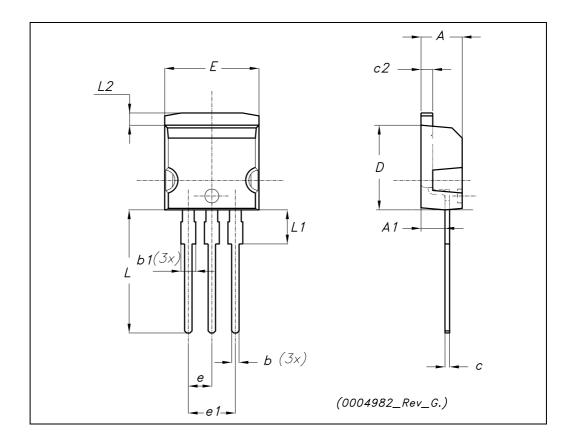
### **TO-220 MECHANICAL DATA**

DIM		mm.		inch		
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
С	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
Е	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øΡ	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



# TO-262 (I<sup>2</sup>PAK) MECHANICAL DATA

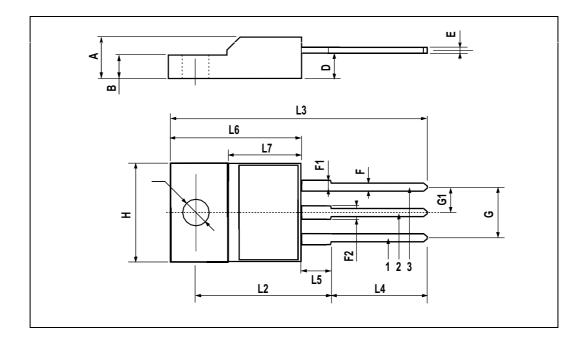
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



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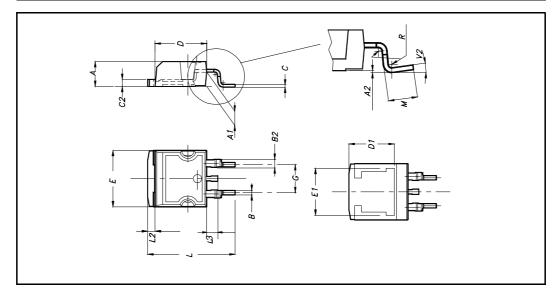
#### **TO-220FP MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
Е	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
Н	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



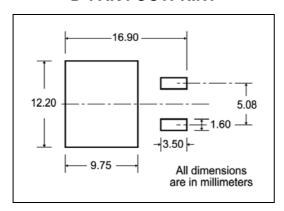
# D<sup>2</sup>PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
М	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		4º			

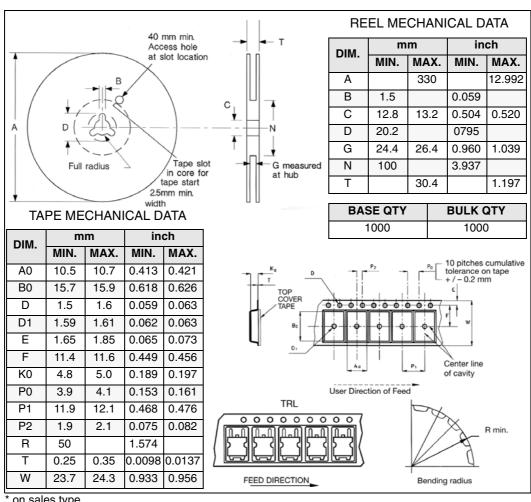


#### 5 Packaging mechanical data

### D<sup>2</sup>PAK FOOTPRINT



#### TAPE AND REEL SHIPMENT



on sales type

# 6 Revision history

Table 9. Document revision history

Date	Revision	Changes	
26-Jul-2004	8	First Release	
17-Feb-2005	9	Insert the TO-247 package	
25-Oct-2006	10	The document has been reformatted	
18-Dec-2006	11	Text updates on Table 5.	
27-Aug-2007	12	Updated Figure 2 and Figure 4	

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